TOSHIBA TG2206F

TOSHIBA GaAs LINEAR INTEGRATED CIRCUIT GaAs MONOLITHIC

# TG2206F

## RF SPDT SWITCH

SWITCH THE RECEIVE FILTER FOR MOBILE COMMUNICATION SWITCH THE DIVERSITY ANTENNA SWITCH THE LOCAL SIGNAL

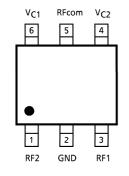
#### **FEATURES**

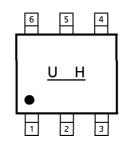
 Low Insertion LOSS :  $L_{OSS} = 0.4 \, dB \, (Typ.)$ High Isolation : ISL = 28 dB (Typ.)Low Voltage Operation :  $V_C = 0 V/2.5 V$ 

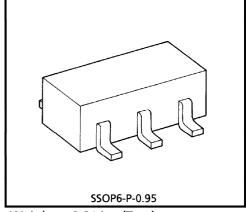
Small Package : SM6 package (2.9\*1.6\*1.1 mm)

#### PIN CONNECTION (TOP VIEW)









Weight: 0.014 g (Typ.)

#### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Control Voltage	V <sub>C1</sub>	5	V
Control Voltage	V <sub>C2</sub>	5	V
Input Power	Pi	1	W
Operating Temperature Range	T <sub>opr</sub>	<b>- 40∼85</b>	°C
Storage Temperature Range	T <sub>stg</sub>	<b>- 55∼125</b>	°C

#### **CAUTION**

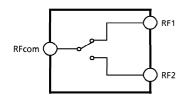
This device is electrostatic sensitivity. Please handle with caution.

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## ELECTRICAL CHARACTERISTICS (f = 1 GHz, Ta = 25°C, $Z_g$ = $Z_l$ = 50 $\Omega$ )

			<u> </u>				
CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Insertion Loss	LOSS (1)	1	$V_{C1} = 2.5 \text{ V}, V_{C2} = 0 \text{ V},$ $P_i = 0 \text{ dBmW}$	_	0.4	0.7	dB
	LOSS (2)	1	$V_{C1} = 0 \text{ V}, V_{C2} = 2.5 \text{ V},$ $P_i = 0 \text{ dBmW}$		0.4	0.7	
Isolation	ISL (1)	1	$V_{C1} = 2.5 \text{ V}, V_{C2} = 0 \text{ V},$ $P_i = 0 \text{ dBmW}$	25	28	I	dB
	ISL (2)	1	$V_{C1} = 0 \text{ V}, V_{C2} = 2.5 \text{ V},$ $P_i = 0 \text{ dBmW}$	25	28	_	
Output Power at 1dB Gain Compression	P <sub>o1dB</sub>	1	$V_{C1} = 2.5 \text{ V}, V_{C2} = 0 \text{ V or}$ $V_{C1} = 0 \text{ V}, V_{C2} = 2.5 \text{ V}$	15	20	_	dBmW
Control Current	l <sub>C1</sub>	_	$V_{C1} = 0 V$ , $V_{C2} = 3 V$ or	_	_	0.01	mΑ
	I <sub>C2</sub>	_	$V_{C1} = 3 V, V_{C2} = 0 V$	_	_	0.01	
Switching Time	t <sub>sw</sub>	_	$V_{C1} = 0 V$ , $V_{C2} = 3 V$ or $V_{C1} = 3 V$ , $V_{C2} = 0 V$	_	0.01	_	$\mu$ s

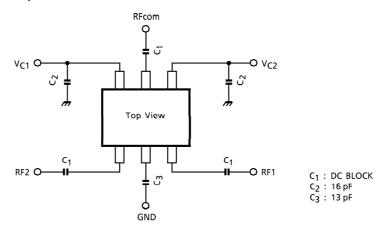
## **BLOCK DIAGRAM**



## **SWITCH CONDITION**

CONTROL VOLTAGE	SWITCH CONDITION
$V_{C1} = 2.5 V$	RFcom-RF1 OFF
$V_{C2} = 0 V$	RFcom-RF2 ON
V <sub>C1</sub> = 0 V	RFcom-RF1 ON
$V_{C2} = 2.5 V$	RFcom-RF2 OFF

### TEST CIRCUIT1 (RF TEST CIRCUIT)



Please fix the value of each capacity for using frequency and circuit.

#### **NOTICE**

The circuits and measurements contained in this document are given only in the context of as examples of applications for these products.

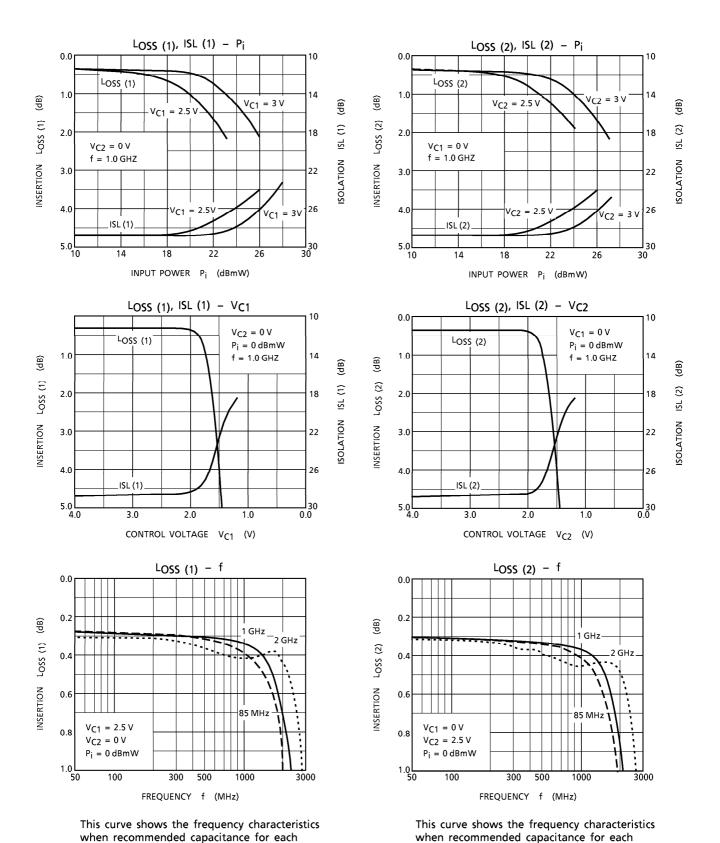
Moreover, these example application circuits are not intended for mass production, since the high-frequency characteristics (the AC characteristics) of these devices will be affected by the external components which the customer uses, by the design of the circuit and by various other conditions. It is the responsibility of the customer to design external circuits which correctly implement the intended application, and to check the characteristics of the design.

TOSHIBA assume no responsibility for the integrity of customer circuit designs or applications.

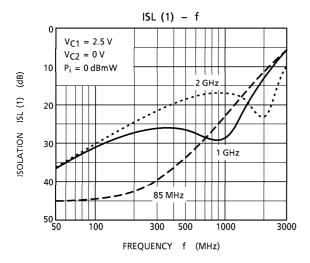
#### RECOMMEND CAPACITY

	85 MHz	0.8~1 GHz	1.6 GHz	2 GHz
C1	100 pF	100 pF	22 pF	9 pF
C2	100 pF	16 pF	10 pF	9 pF
C3	150 pF	13 pF	4 pF	3 pF

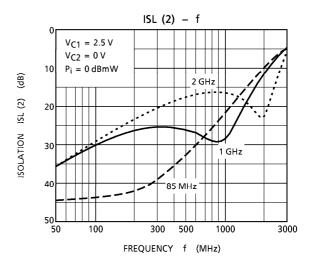
frequency added.



frequency added.



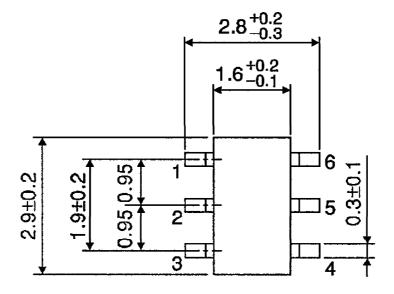
This curve shows the frequency characteristics when recommended capacitance for each frequency added.

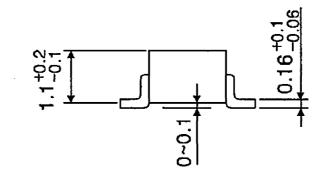


This curve shows the frequency characteristics when recommended capacitance for each frequency added.

## PACKAGE DIMENSIONS SSOP6-P-0.95

Unit: mm





Weight: 0.014 g (Typ.)